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(54) **SEMICONDUCTOR DEVICE AND  
MANUFACTURING METHOD OF THE  
SEMICONDUCTOR DEVICE**

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(57) **ABSTRACT**

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**Related U.S. Application Data**

(60) Continuation of application No. 18/076,808, filed on Dec. 7, 2022, which is a continuation-in-part of application No. 17/900,429, filed on Aug. 31, 2022, now Pat. No. 11,889,697, which is a division of application No. 16/863,608, filed on Apr. 30, 2020, now Pat. No. 11,462,557.

A semiconductor device and a method of manufacturing the semiconductor device are provided. The semiconductor device includes a source structure formed on a base, an etch prevention layer formed on the source structure, bit lines, a stack structure located between the etch prevention layer and the bit lines and including conductive layers and insulating layers that are alternately stacked on each other; and a source contact structure extending into the stack structure in a vertical direction to be coupled to the source structure, wherein the source contact structure includes polysilicon.

